







Electrical Optical Characteristics at Ta=25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Condition
Radiant Intensity	Ie	2.2	3.0	4.4	mW/sr	I _F =20mA (Note 1,3)
Viewing Angle	1/2		130		Deg.	(Note 2)
Peak Wavelength			940		nm	I _F =20mA
Spectral Line Half- Width			50		nm	I _F =20mA
Forward Voltage	V_{F}		1.25	1.60	V	I _F =50mA
Reverse Current	I_R			100	μА	V _R =5V

Note:

- 1. Point sources of the amount of radiation per unit time in a given direction within the unit solid Angle radiated energy.
- 2. _{1/2} is the off-axis angle at which the Radiant Intensity is half the axial Radiant Intensity.
- 3. The Ie guarantee should be added $\pm 15\%$ tolerance.

Infrared Emitting Diode Specification

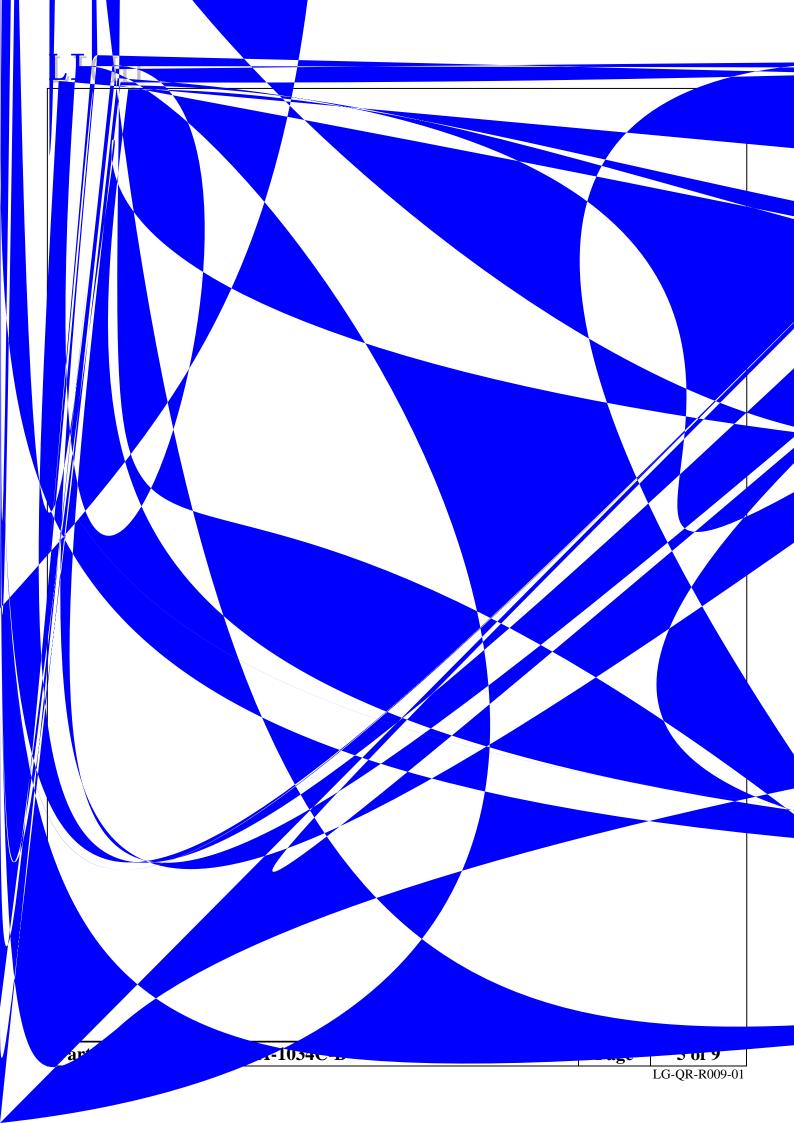
●Commodity: Infrared emitting diode

●Intensity Bin Limits (At 20mA)

BIN CODE	Min. (mW/sr)	Max. (mW/sr)
18	2.2	2.6
19	2.6	3.1
20	3.1	3.7
21	3.7	4.4

NOTE: The Ie guarantee should be added ±15% tolerance.

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ED MOUNTING METHOD 1. The lead pitch of the LED must match the pitch of the mounting holes on the PCB during component placement. Lead-forming may be required to insure the lead pitch matches the hole pitch. Refer to the figure below for proper lead forming procedures (Fig.1).	

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